



SD103A - SD103C

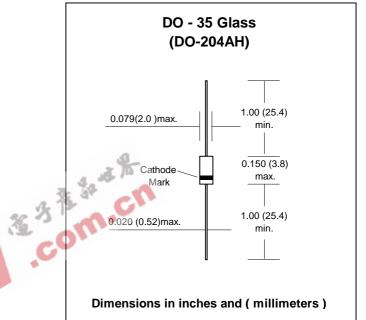
FEATURES:

- For general purpose applications
- The SD103 series is a Metal-on-silicon Schottky barrier device which is protected by a PN junction guard ring.
- The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications.
- Other applications are click suppression, efficient full wave bridges in telephone subsets, and blocking diodes in rechargeable low voltage battery systems.
- These diodes are also available in the MiniMELF case with type designations LL103A thru LL103C.
- Pb / RoHS Free

MECHANICAL DATA :

Case: DO-35 Glass Case Weight: approx. 0.13g

SCHOTTKY BARRIER DIODES



Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified.)

Parameter		Symbol	Value	Unit	
	SD103A		40		
Repetitive Peak Reverse Voltage	SD103B	V _{RRM}	30	V	
	SD103C		20		
Single Cycle Surge 60 Hz Sine Wave		I _{FSM}	15	А	
Power Dissipation (Infinite Heatsink)		PD	400 ⁽¹⁾	mW	
Thermal Resistance Junction to Ambient Air		$R_{ extsf{ heta}JA}$	0.3 ⁽¹⁾	°C/mW	
Junction Temperature		TJ	125 ⁽¹⁾	°C	
Storage temperature range		Ts	-55 to + 150 ⁽¹⁾	°C	

Note: (1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature.

Electrical Characteristics ($T_J = 25^{\circ}C$ unless otherwise noted)

Parameter		Symbol	Test Condition	Min	Тур	Max	Unit
Reverse Current	SD103A		V _R = 30 V	-	-	5	
	SD103B	I _R	V _R = 20 V	-	-	5	μA
	SD103C		V _R = 10 V	-	-	5	
Forward Voltage Drop		V _F	$I_F = 20 \text{mA}$	-	-	0.37	V
			$I_F = 200 \text{mA}$	-	-	0.6	
Junction Capacitance		Ctot	$V_R = 0 V, f = 1MHz$	-	50	-	pF
Reverse Recovery Time		Trr	$I_F = I_R = 50$ mA to 200mA recover to $0.1I_R$	-	10	-	ns





